

# Gheorghe Pristavu

## List of Publications by Year in descending order

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36  
papers

207  
citations

1307543

7  
h-index

1474186

9  
g-index

36  
all docs

36  
docs citations

36  
times ranked

181  
citing authors

#	ARTICLE	IF	CITATIONS
1	PLL-Based Readout Circuit for SiC-MOS Capacitor Hydrogen Sensors in Industrial Environments. Sensors, 2022, 22, 1462.	3.8	3
2	60–700 K CTAT and PTAT Temperature Sensors with 4H-SiC Schottky Diodes. Sensors, 2021, 21, 942.	3.8	12
3	Detecting anomalous behavior in Si MOS capacitors. , 2021, , .		0
4	Experimental Comparison of 8-bit Digitally Programmable Potentiometers based on Multistage Architectures. , 2021, , .		0
5	Enhanced Non-Uniformity Modeling of 4H-SiC Schottky Diode Characteristics Over Wide High Temperature and Forward Bias Ranges. IEEE Journal of the Electron Devices Society, 2020, 8, 1339-1344.	2.1	7
6	Electrical defects in grown oxide on SiC and from the oxide/SiC interface. , 2020, , .		0
7	Characterization of non-uniform Ni/4H-SiC Schottky diodes for improved responsivity in high-temperature sensing. Materials Science in Semiconductor Processing, 2019, 94, 64-69.	4.0	27
8	400 Å°C Sensor Based on Ni/4H-SiC Schottky Diode for Reliable Temperature Monitoring in Industrial Environments. Sensors, 2019, 19, 2384.	3.8	20
9	Voltage Controlled Oscillator for Small-Signal Capacitance Sensing. , 2019, , .		1
10	Nickel silicide compounds investigation obtained at low and high temperatures. , 2019, , .		1
11	Improved Ti/Pt/Au - n-Type Si Contacts by Post-Metallization Annealing in Nitrogen Atmosphere. , 2018, , .		0
12	High Temperature Behavior Prediction Techniques for Non-Uniform Ni/SiC Schottky Diodes. Materials Science Forum, 2018, 924, 967-970.	0.3	2
13	Oxide trap states versus gas sensing in SiC-MOS capacitors – The effect of N- and P- based post oxidation processes. Sensors and Actuators B: Chemical, 2017, 245, 911-922.	7.8	8
14	Experimental characterization of a high accuracy amperometric sense and control circuit for three-electrode biosensors. , 2017, , .		1
15	SiO <sub>2</sub> /SiC interface improvements using an oxidized thin film of a-Si. , 2016, , .		0
16	Smart sensor for chemical compounds concentration. , 2016, , .		1
17	A new 4H-SiC hydrogen sensor with oxide ramp termination. Materials Science in Semiconductor Processing, 2016, 42, 268-272.	4.0	10
18	SiO <sub>2</sub> /4H-SiC interface states reduction by POCl <sub>3</sub> post-oxidation annealing. , 2015, , .		2

#	ARTICLE	IF	CITATIONS
19	High temperature sensors based on silicon carbide (SiC) devices. , 2015, , .		13
20	Suppressing start-up time variation versus load current &#x2014; Adaptive soft-start in boost LED drivers. , 2015, , .		5
21	High voltage freewheeling diodes in an extended capability LED driving application. , 2015, , .		0
22	Fading circuit for linear/exponential current variations in boost converters for LED driving. , 2015, , .		0
23	Application enhancement for driving large strings of LEDs. , 2014, , .		1
24	Temperature behavior of 4H-SiC MOS capacitor used as a gas sensor. , 2014, , .		8
25	Variable Off-Time Control Loop for Current-Mode Floating Buck Converters in LED Driving Applications. IEEE Journal of Solid-State Circuits, 2014, 49, 1571-1579.	5.4	42
26	Less is more &#x2014; The improved variable OFF time current-mode floating buck controller. , 2013, , .		2
27	Forcing the limits &#x2014; Peak voltage extension for floating buck controller. , 2013, , .		2
28	Variable off time current-mode floating buck controller - A different approach. , 2013, , .		5
29	Time modulation &#x2014; The exponential way. , 2012, , .		4
30	Overcoming leakage current by output precharging in error amplifiers. , 2012, , .		3
31	Offset cancellation in bandgap references with CMOS operational amplifiers. , 2011, , .		2
32	Fully-integrated oscillator in CMOS technology. , 2010, , .		1
33	Two Packaging Solutions for High Temperature SiC Diode Sensors. Materials Science Forum, 0, 778-780, 1063-1066.	0.3	10
34	Electrical Characterization of Ni-Silicide Schottky Contacts on SiC for High Performance Temperature Sensor. Materials Science Forum, 0, 821-823, 436-439.	0.3	4
35	An Investigation of SiC Schottky Contact Barrier Inhomogeneity for Temperature Sensing Applications. Materials Science Forum, 0, 858, 577-581.	0.3	3
36	Barrier Stability of Pt/4H-SiC Schottky Diodes Used for High Temperature Sensing. Materials Science Forum, 0, 897, 606-609.	0.3	7